

QH 2822 #



RECORDED

93 MAR 25 1982 50

1987年1月2日于北京

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes  
Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH  
  
Docket No.: 303.229US2 Serial No.: 09/132,157  
Filed: August 11, 1998 Due Date: March 15, 1999  
Examiner: Mark Prenty Group Art Unit: 2822

**Assistant Commissioner for Patents  
Washington, D.C. 20231**

We are transmitting herewith the following attached items (as indicated with an "X"):

- A return postcard.  
 An Amendment and Response (14 Pages).  
 A Supplemental Information Disclosure Statement (1 pgs.), Form 1449 (1 pgs.), and copies of 1 cited references.  
 A check in the amount of \$240.00 to cover the fee for consideration of Information Disclosure Statement under 97(c).

**Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.**

**CERTIFICATE UNDER 37 CFR 1.8:** The undersigned hereby certifies that this Transmittal Letter and the paper, as described above, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on this 15th day of March, 1999. 

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By: Thomas W. Leffert  
Atty: Thomas W. Leffert  
Reg. No. 40,697

(GENERAL)